

800V N-Channel MOSFET

FEATURES

- Fast switching
- 100% avalanche tested
- Improved dv/dt capability

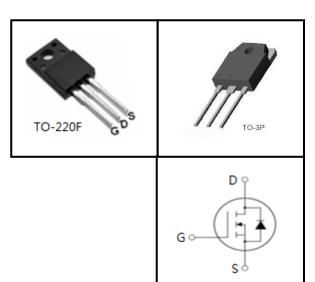
APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)

Device Marking and Package Information			
Device	Package	Marking	
CS12N80F	TO-220F	CS12N80F	
CS12N80V	TO-3P	CS12N80V	

Absolute Maximum Ratings $T_c = 25^{\circ}C$, unless otherwise noted					
Parameter		Symbol	Va		
			TO-220F	ТО-3Р	Unit
Drain-Source Voltage (V _{GS} = 0V)		V _{DSS}	800		V
Continuous Drain Current		I _D	12		A
Pulsed Drain Current	(note1)	I _{DM}	48		A
Gate-Source Voltage		V _{GSS}	±	30	V
Single Pulse Avalanche Energy	(note2)	E _{AS}	460.8		mJ
Avalanche Current	(note1)	I _{AS}	9.6		A
Repetitive Avalanche Energy	(note1)	E _{AR}	276.5		mJ
Power Dissipation (T _C = 25°C)		P _D	25 70		W
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55~+150		°C

Thermal Resistance				
Beremeter	Symphol	Va	Unit	
Parameter	Symbol	TO-220F	TO-3P	Unit
Thermal Resistance, Junction-to-Case	R _{thJC}	5	1.78	
Thermal Resistance, Junction-to-Ambient	R _{thJA}	62.5	60	K/W





CS12N80F, CS12N80V

Specifications $T_J = 25^{\circ}C$, unless otherwise noted							
Parameter	Symbol	Test Conditions	Value			11	
		Test conditions	Min.	Тур.	Max.	Unit	
Static			_				
Drain-Source Breakdown Voltage	V _{(BR)DSS}	$V_{GS} = 0V, I_{D} = 250 \mu A$	800			V	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 800V, V_{GS} = 0V, T_{J} = 25^{\circ}C$			1	μA	
Gate-Source Leakage	I _{GSS}	V_{GS} = $\pm 30V$			±100	nA	
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250 \mu A$	3.0		4.0	V	
Drain-Source On-Resistance (Note3)	$R_{DS(on)}$	V _{GS} = 10V, I _D =6A		0.67	0.8	Ω	
Dynamic							
Input Capacitance	C _{iss}			2115		pF	
Output Capacitance	C _{oss}	$V_{GS} = 0V,$ $V_{DS} = 25V,$		217			
Reverse Transfer Capacitance	C _{rss}	f = 1.0MHz		43			
Total Gate Charge	Q_{g}	$V_{DD} = 640V, I_{D} = 12A,$ $V_{GS} = 10V$		88		nC	
Gate-Source Charge	Q_{gs}			10			
Gate-Drain Charge	Q_{gd}			49			
Turn-on Delay Time	t _{d(on)}			50		ns	
Turn-on Rise Time	t _r	V _{DD} = 400V, I _D = 12A,		44			
Turn-off Delay Time	t _{d(off)}	$V_{DD} = 400V, I_D = 12A, \\ R_G = 25 \ \Omega$		362			
Turn-off Fall Time	t _f			80			
Drain-Source Body Diode Character	istics						
Continuous Body Diode Current	۱ _s				12	A	
Pulsed Diode Forward Current	I _{SM}	T _C = 25 °C			48		
Body Diode Voltage	V_{SD}	$T_J = 25^{\circ}C, I_{SD} = 6A, V_{GS} = 0V$			1.4	V	
Reverse Recovery Time	t _{rr}	V _{GS} = 0V,I _S = 12A,		639		ns	
Reverse Recovery Charge	Q _{rr}	di _F /dt =100A /µs		3		μC	

Notes

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature
- 2. L=10mH, V_{DD} = 50V, R_{G} = 25 Ω , Starting T_{J} = 25 °C
- 3. Pulse Test: Pulse width \leq 300µs, Duty Cycle \leq 1%



12

10

8

6

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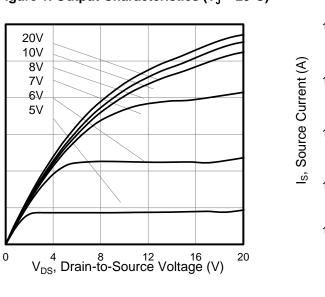
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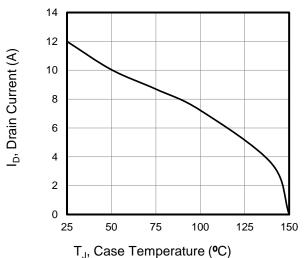
I_D, Drain Current (A)

Typical Characteristics $T_J = 25^{\circ}C$, unless otherwise noted

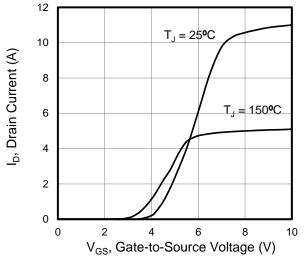
Figure 1. Output Characteristics ($T_J = 25^{\circ}C$)











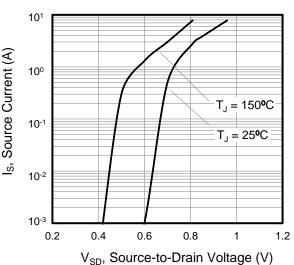


Figure 2. Body Diode Forward Voltage

Figure 4. BV_{DSS} Variation vs. Temperature

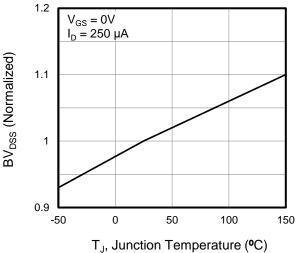
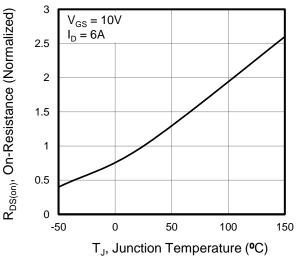
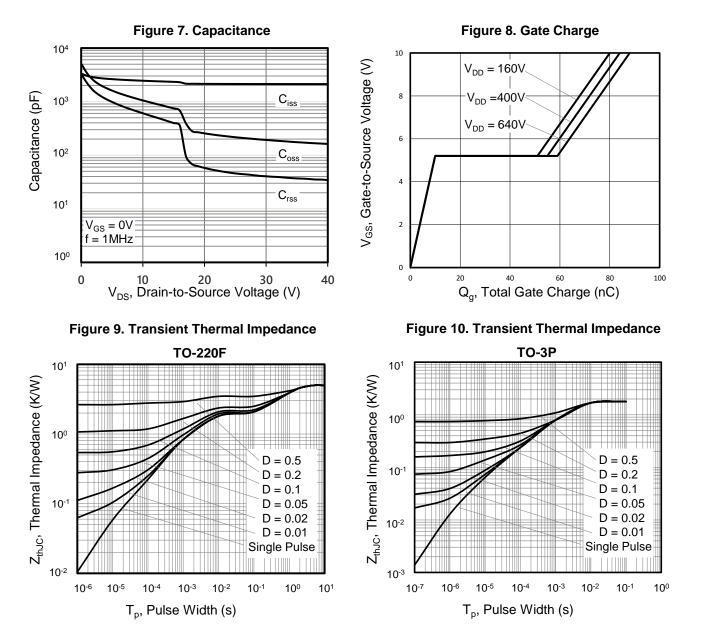


Figure 6. On-Resistance vs. Temperature





Typical Characteristics $T_J = 25^{\circ}C$, unless otherwise noted







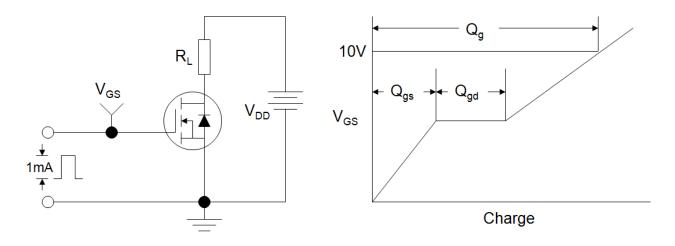


Figure B: Resistive Switching Test Circuit and Waveform

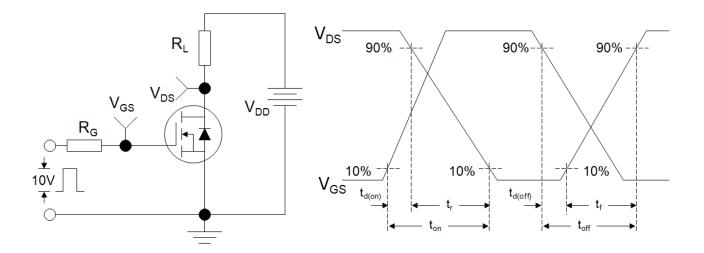
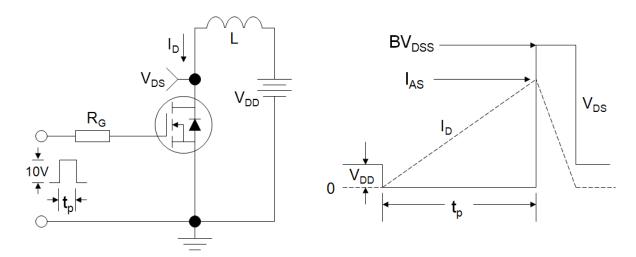


Figure C: Unclamped Inductive Switching Test Circuit and Waveform

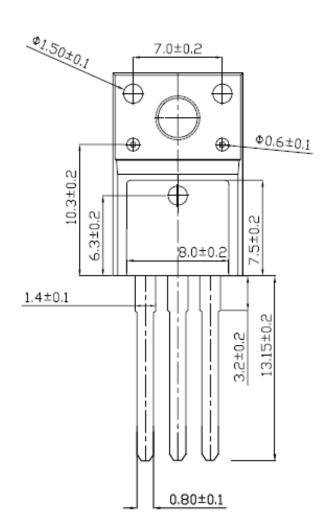


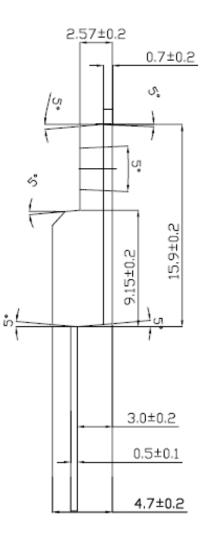
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TO-220F

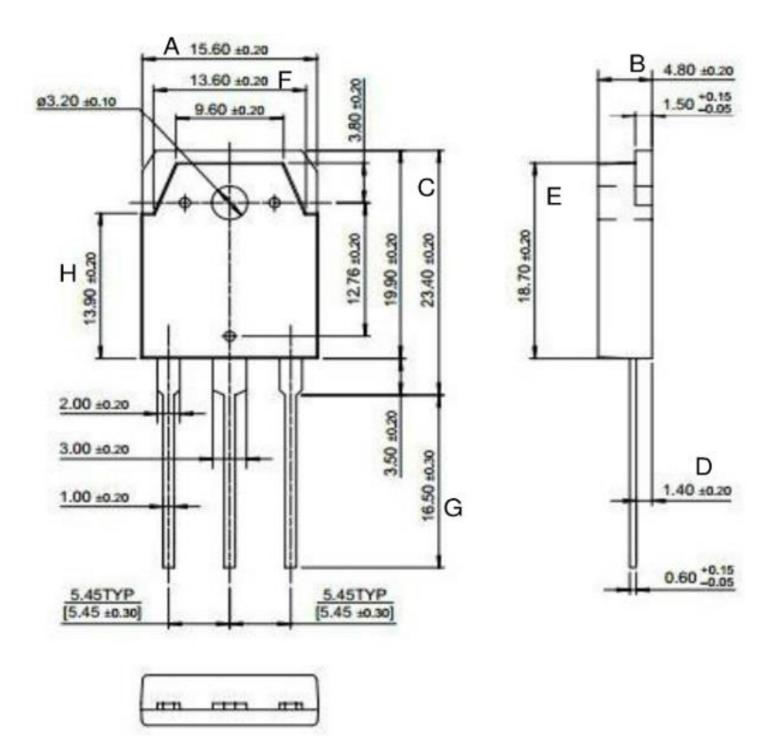








TO-3P





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